



6-A Silicon Triacs

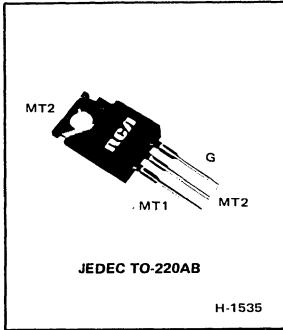
Three-Lead Plastic Types for Power-Control and Power-Switching Applications

Features:

- 60-A Peak Surge Full-Cycle Current Ratings
- Shorted-Emitter, Center-Gate Design
- Package Design Facilitates Mounting on a Printed-Circuit Board
- Low Switching Losses
- Low Thermal Resistance

Voltage Package	200 V Type	400 V Type
TO-220AB	T2500B (41014)	T2500D (41015)

Numbers in parentheses are former RCA type numbers.



Types T2500B and T2500D* are gate-controlled full-wave silicon triacs utilizing a plastic case with three leads to facilitate mounting on printed-circuit boards. They are intended for the control of ac loads in such applications as motor controls, heating controls, relay replacement, solenoid drivers, static switching, and power-switching systems.

These devices are designed to switch from an off-state to an on-state for either polarity of applied voltage with positive or

negative gate triggering voltages. They have an on-state current rating of 6 amperes at a T_C of 80°C and repetitive off-state voltage ratings of 200 volts and 400 volts, respectively.

The unique plastic package design provides not only ease of mounting but also low terminal impedance, which allows operation at high case temperatures and permits reduced heat-sink size.

*Formerly RCA Dev. Nos. TA8504 and TA8505.

MAXIMUM RATINGS, Absolute-Maximum Values:

For Operation with Sinusoidal Supply Voltage at Frequencies up to 50/60 Hz and with Resistive or Inductive Load.

REPETITIVE PEAK OFF-STATE VOLTAGE:[●]

Gate open, $T_J = -65$ to 100°C

	T2500B	T2500D	
V_{DROM}	200	400	V

RMS ON-STATE CURRENT (Conduction angle = 360°):

Case temperature

$T_C = 80^\circ\text{C}$

$I_T(\text{RMS})$	6	A
	See Fig. 3	

For other conditions

PEAK SURGE (NON-REPETITIVE) ON-STATE CURRENT:

For one cycle of applied principal voltage, $T_C = 80^\circ\text{C}$

60 Hz (sinusoidal)

50 Hz (sinusoidal)

I_{TSM}	60	A
	50	A
	See Fig. 4	

For more than one cycle of applied principal voltage.

RATE OF CHANGE OF ON-STATE CURRENT:

$V_{DM} = V_{DROM}$, $I_{GT} = 200$ mA, $t_r = 0.1$ μs (See Fig. 16)

di/dt	70	A/ μs
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FUSING CURRENT (for Triac Protection):

$T_C = -65$ to 100°C , $t = 1.25$ to 10 ms.

I^2t	18	A ² s
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PEAK GATE-TRIGGER CURRENT:[■]

For 10 μs max; see Fig. 10

I_{GTM}	4	A
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GATE POWER DISSIPATION:

Peak (For 1 μs max., $I_{GTM} \leq 4$ A; see Fig. 10)

P_{GM}	16	W
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AVERAGE

$P_G(\text{AV})$	0.2	W
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TEMPERATURE RANGE:[▲]

Storage

T_{stg}	-65 to 150	$^\circ\text{C}$
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Operating (Case)

T_C	-65 to 100	$^\circ\text{C}$
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TERMINAL TEMPERATURE (During soldering):

For 10 s max. (terminals and case)

T_T	225	$^\circ\text{C}$
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- For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.
- For either polarity of gate voltage (V_G) with reference to main terminal 1.
- ▲ For temperature measurement reference point, see *Dimensional Outline*.

ELECTRICAL CHARACTERISTICS at Maximum Ratings unless otherwise specified, and at indicated Case Temperature (T_C)

CHARACTERISTIC	SYMBOL	LIMITS						UNITS
		T2500B			T2500D			
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Peak Off-State Current:* Gate Open, $V_{DROM} = \text{Max. rated value}$ At $T_J = 100^\circ\text{C}$	I_{DROM}	-	0.1	2	-	0.1	2	mA
Maximum On-State Voltage:* For $i_T = 30 \text{ A (peak)}$ and $T_C = 25^\circ\text{C}$	V_{TM}	-	1.7	2	-	1.7	2	V
DC Holding Current:* Gate Open Initial principal current = 150 mA (dc) At $T_C = 25^\circ\text{C}$	I_{HO}	-	15	30	-	15	30	mA
For other case temperatures	See Fig. 8.							
Critical Rate of Rise of Commutation Voltage:* [†] For $v_D = V_{DROM}$, $I_T(\text{RMS}) = 6 \text{ A}$, Commutating $di/dt = 3.2 \text{ A/ms}$, and gate unenergized At $T_C = 80^\circ\text{C}$	dv/dt	4	10	-	4	10	-	$V/\mu\text{s}$
Critical Rate of Rise of Off-State Voltage:* For $v_D = V_{DROM}$, exponential voltage rise, and gate open At $T_C = 100^\circ\text{C}$	dv/dt	100	300	-	75	250	-	$V/\mu\text{s}$
For other case temperatures	See Fig. 9							
DC Gate-Trigger Current:* [†] For $v_D = 12 \text{ V (dc)}$, $R_L = 12 \Omega$ $T_C = 25^\circ\text{C}$, and specified triggering mode: I^+ Mode (V_{MT2} positive, V_G positive)	I_{GT}	-	10	25	-	10	25	mA
III^- Mode (V_{MT2} negative, V_G negative)		-	15	25	-	15	25	
I^- Mode (V_{MT2} positive, V_G negative)		-	20	60	-	20	60	
III^+ Mode (V_{MT2} negative, V_G positive)		-	30	60	-	30	60	
For other case temperatures		See Figs. 12 and 13						
DC Gate-Trigger Voltage:* [†] For $v_D = 12 \text{ V (dc)}$ and $R_L = 12 \Omega$ At $T_C = 25^\circ\text{C}$	V_{GT}	-	1.25	2.5	-	1.25	2.5	V
For other case temperatures		See Fig. 14.						
For $v_D = V_{DROM}$ and $R_L = 125 \Omega$ At $T_C = 100^\circ\text{C}$		0.2	-	-	0.2	-	-	
Gate-Controlled Turn-On Time (Delay Time + Rise Time): For $v_D = V_{DROM}$, $I_{GT} = 160 \text{ mA}$, rise time = $0.1 \mu\text{s}$, and $i_T = 10 \text{ A (peak)}$ At $T_C = 25^\circ\text{C}$ (See Fig. 15.)	t_{gt}	-	1.6	2.5	-	1.6	2.5	μs
Thermal Resistance: Junction-to-Case	$R_{\theta JC}$	-	-	2.7	-	-	2.7	$^\circ\text{C/W}$
Junction-to-Ambient	$R_{\theta JA}$	-	-	60	-	-	60	$^\circ\text{C/W}$

*For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.

[†]For either polarity of gate voltage (V_G) with reference to main terminal 1.

[‡]Variants of these devices having dv/dt characteristics selected specifically for inductive loads are available on special order; for additional information, contact your RCA Representative or your RCA Distributor.

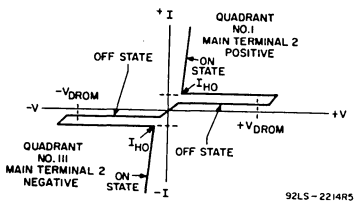


Fig. 1—Principal voltage-current characteristic.

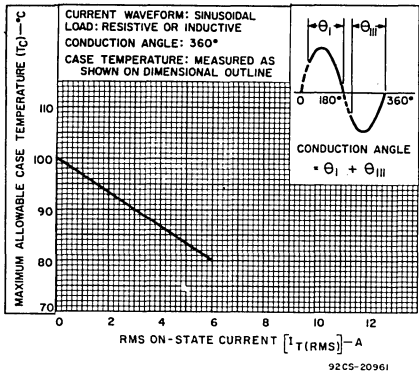


Fig. 3—Allowable case temperature vs. on-state current.

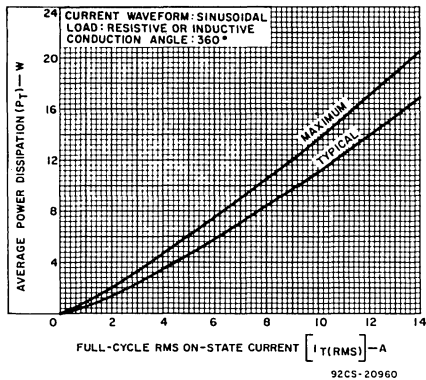


Fig. 2—Power dissipation vs. on-state current.

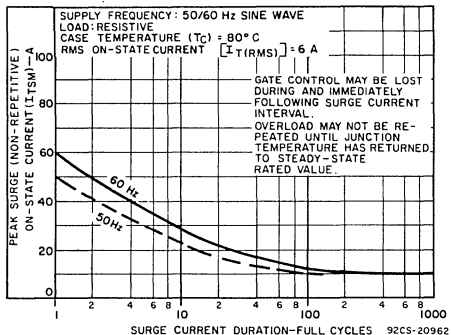


Fig. 4—Peak surge on-state current vs. surge current duration.

$$t_{gt} = t_d + t_r$$

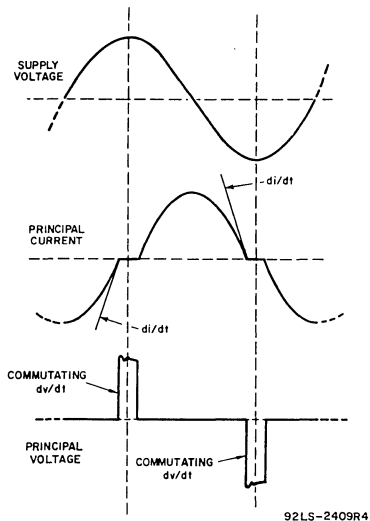


Fig. 5—Oscilloscope display of commutating dv/dt .

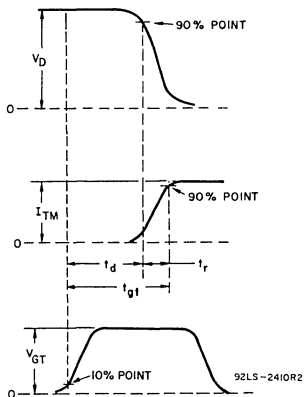


Fig. 6—Oscilloscope display for measurement of gate-controlled turn-on time (t_{gt}).

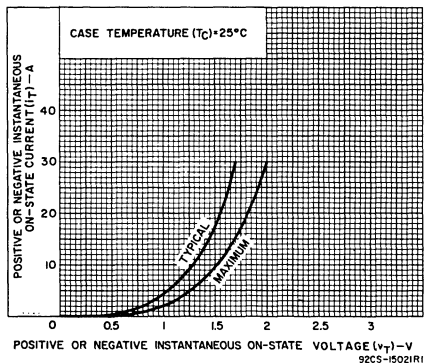


Fig. 7—On-state current vs. on-state voltage.

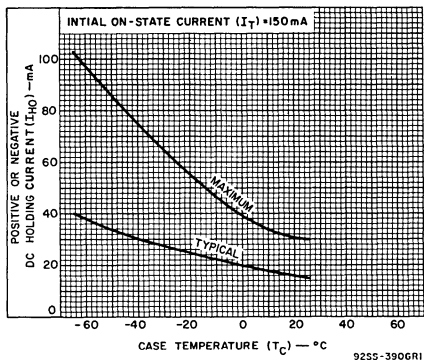


Fig. 8—DC holding current for either direction of on-state current vs. case temperature.

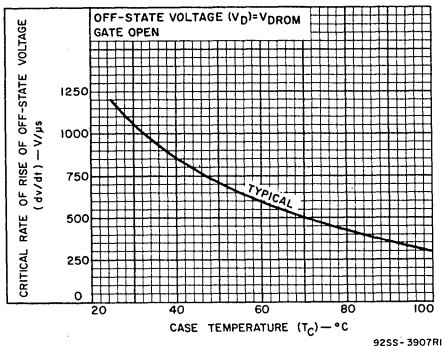


Fig. 9—Critical rate of rise of off-state voltage vs. case temperature.

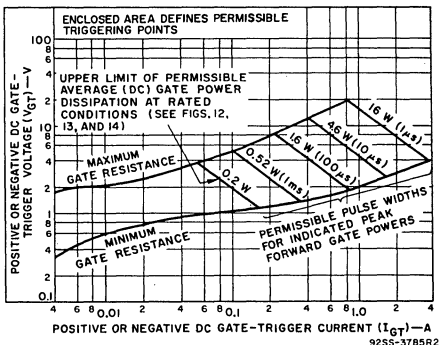
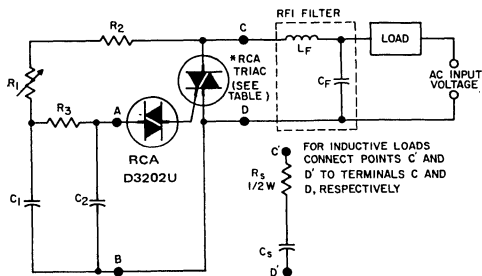


Fig. 10—Gate pulse characteristics for all triggering modes.



	120V	240V
C_s	0.047 μ F/200 V	0.047 μ F/400 V
R_s	1.8 K Ω	1.8 K Ω

92CS-20963R1

AC INPUT VOLTAGE	C_1	C_2	R_1	R_2	R_3	RFI FILTER		RCA TYPES
						L_F^* (typ.)	C_F^* (typ.)	
120 V 60 Hz	0.1 μ F 200 V	0.1 μ F 100 V	100 K Ω ½ W	2.2 K Ω ½ W	15 K Ω ½ W	100 μ H	0.1 μ F 200V	T2500B
240 V 50 Hz	0.1 μ F 400 V	0.1 μ F 100 V	250 K Ω 1 W	3.3 K Ω ½ W	15 K Ω ½ W	200 μ H	0.1 μ F 400 V	T2500D
240 V 60 Hz	0.1 μ F 400 V	0.1 μ F 100 V	200 K Ω 1 W	3.3 K Ω ½ W	15 K Ω ½ W	200 μ H	0.1 μ F 400 V	T2500D

*Typical values for lamp-dimming circuits.

Fig. 11—Typical phase-control circuit for lamp dimming, heat controls, and universal motor speed controls.

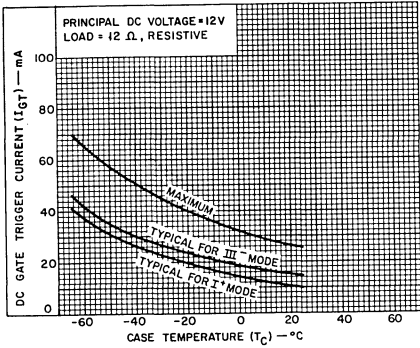


Fig. 12—DC gate-trigger current (for I⁺ and III⁻ triggering modes) vs. case temperature.

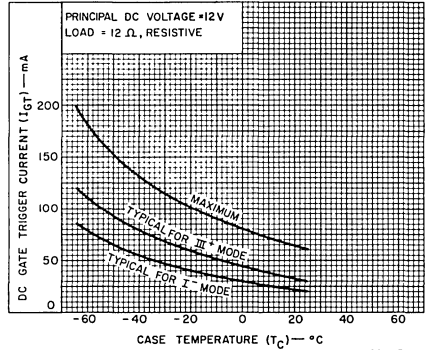


Fig. 13—DC gate-trigger current (for I⁻ and III⁺ triggering modes) vs. temperature.

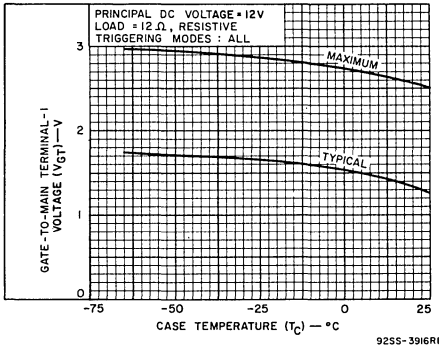


Fig. 14—DC gate-trigger voltage vs. case temperature.

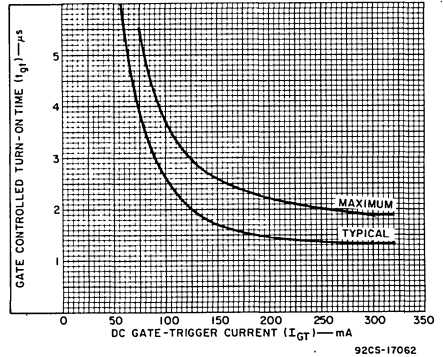


Fig. 15—Typical turn-on time vs. gate-trigger current.

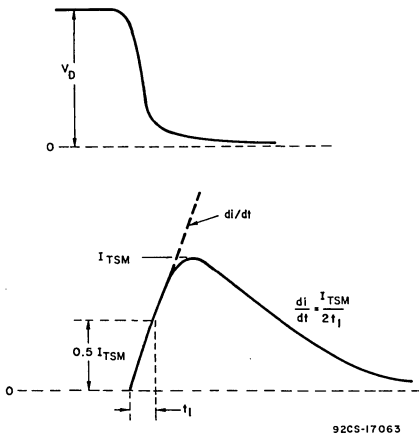


Fig. 16—Rate-of-change of on-state current with time (defining di/dt).

TERMINAL CONNECTIONS

- Lead No. 1—Main Terminal 1
- Lead No. 2—Main Terminal 2
- Lead No. 3—Gate
- Mounting Flange—Main Terminal 2